

LM3211 Step-up PWM DC/DC Converter Integrated with 4 Buffers

Check for Samples: LM3211

FEATURES

- 1.4A, 0.17Ω, Internal Power Switch
- V_{IN} Operating Range: 2.2V to 7.5V
- 600kHz/1.25MHz Selectable Frequency Step-Up **DC/DC Converter**
- 20 Pin TSSOP Package
- **Inrush Current Limiting Circuitry**
- **External Softstart Override**
- 4 Gamma Buffers

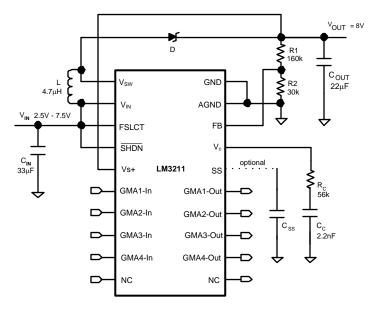
APPLICATIONS

- **LCD Bias Supplies**
- **Handheld Devices**
- **Portable Applications**
- **Cellular Phones/Digital Cameras**

DESCRIPTION

The LM3211 is a compact bias solution for TFT displays. It has a current mode PWM step-up DC/DC converter with a 1.4A, 0.17Ω internal switch. Capable of generating 8V at 300mA from a Lithium Ion battery, the LM3211 is ideal for generating bias voltages for large screen LCD panels. The LM3211 can be operated at switching frequencies of 600kHz or 1.25MHz, allowing for easy filtering and low noise. An external compensation pin gives the user flexibility in setting frequency compensation, which makes possible the use of small, low ESR ceramic capacitors at the output. The LM3211 uses a patented internal circuitry to limit startup inrush current of the boost switching regulator without the use of an external softstart capacitor. An external softstart pin enables the user to tailor the softstart to a specific application. The LM3211 contains 4 Gamma buffers capable of supplying 35mA source and sink. The TSSOP-20 package ensures a low profile overall solution.

Typical Application Circuit



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Connection Diagram

Top View

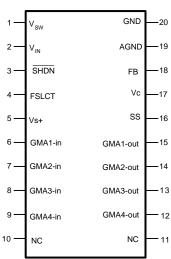


Figure 1. TSSOP 20 Package T_{JMAX} = 125°C, θ_{JA} = 120°C/W ⁽¹⁾ See Package Number PW (R-PDSO-G20)

PIN DESCRIPTION

Pin	Name	Function
1	V _{SW}	Power switch input.
2	V _{IN}	Switching Regulator Power input.
3	SHDN	Shutdown pin, active low.
4	FSLCT	Frequency Select pin. FSLCT = V_{IN} for 1.25 MHz, FSLCT = AGND or floating for 600kHz.
5	Vs+	Gamma Buffer input supply.
6	GMA1-in	Gamma Buffer input.
7	GMA2-in	Gamma Buffer input.
8	GMA3-in	Gamma Buffer input.
9	GMA4-in	Gamma Buffer input.
10	NC	No Connection, leave open.
11	NC	No Connection, leave open.
12	GMA4-out	Gamma Buffer output.
13	GMA3-out	Gamma Buffer output.
14	GMA2-out	Gamma Buffer output.
15	GMA1-out	Gamma Buffer output.
16	SS	Soft start pin.
17	V _C	Boost Compensation Network Connection.
18	FB	Output Voltage Feedback input.
19	AGND	Gamma Buffer ground, Analog ground connection for Regulator.
20	GND	Switch Power Ground.

⁽¹⁾ The maximum allowable power dissipation is a function of the maximum junction temperature, $T_J(MAX)$, the junction-to-ambient thermal resistance, θ_{JA} , and the ambient temperature, T_A . See the Electrical Characteristics table for the thermal resistance of various layouts. The maximum allowable power dissipation at any ambient temperature is calculated using: $P_D(MAX) = (T_{J(MAX)} - T_A)/\theta_{JA}$. Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown.



Pin Functions

V_{sw}(Pin 1): This is the drain of the internal NMOS power switch. Minimize the metal trace area connected to this pin to minimize EMI.

 $V_{IN}(Pin\ 2)$: Input Supply Pin. Bypass this pin with a capacitor as close to the device as possible. The capacitor should connect between V_{IN} and GND.

SHDN(Pin 3): Shutdown Pin. The shutdown pin signal is active low. A voltage of less than 0.3V disables the device. A voltage greater than 0.85V enables the device.

FSLCT(Pin 4): Frequency Select Pin. Connecting FSLCT to AGND selects a 600 kHz operating frequency for the switching regulator. Connecting FSLCT to V_{IN} selects a 1.25 MHz operating frequency. If FSLCT is left floating, the switching frequency defaults to 600 kHz.

Vs+(Pin 5): Supply pin for the four Gamma buffers. Bypass this pin with a capacitor as close to the device as possible. The capacitor should connect between Vs+ and GND.

GMA1-in(Pin 6):Gamma Buffer input pin.

GMA2-in(Pin 7): Gamma Buffer input pin.

GMA3-in(Pin 8): Gamma Buffer input pin.

GMA4-in(Pin 9): Gamma Buffer input pin.

NC(Pin 10):No Connection.

NC(Pin 11): No Connection.

GMA4-out(Pin 12): Gamma Buffer output pin.

GMA3-out(Pin13): Gamma Buffer output pin.

GMA2-out(Pin 14): Gamma Buffer output pin.

GMA1-out(Pin 15): Gamma Buffer output pin.

SS(Pin 16): Softstart pin. Connect capacitor to SS pin and AGND to slowly ramp inductor current on startup.

 $V_c(Pin 17)$: Compensation Network for Boost switching regulator. Connect resistor/capacitor network between V_c pin and AGND for boost switching regulator AC compensation.

FB(Pin 18): Feedback pin. Set the output voltage by selecting values of R1 and R2 using:

$$R1 = R2\left(\frac{V_{OUT}}{1.265V} - 1\right)$$

Connect the ground of the feedback network to the AGND plane, which can be tied directly to the GND pin.

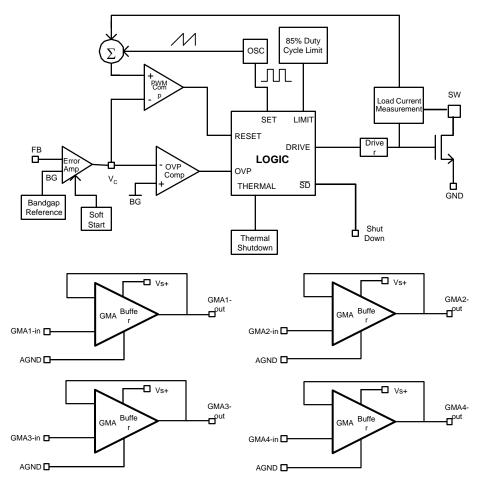
AGND(Pin 19): Analog ground pin. Ground connection for the Gamma buffers and the boost switching regulator. AGND must be tied directly to GND at the pins.

GND(Pin 20): Power ground pin. Ground connection for the NMOS power device of the boost switching regulator. GND must be tied directly to AGND at the pins.

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Block Diagram





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



Absolute Maximum Ratings(1)

V _{IN}		-0.3V to 7.5V
V _{SW} Voltage		-0.3V to 18V
FB Voltage	-0.3V to 7V	
V _C Voltage		0.965V to 1.565V
SHDN Voltage		-0.3V to V _{IN}
FSLCT Voltage		AGND to V _{IN}
Supply Voltage, Vs+		-0.3V to 14V
Buffer Input Voltage		Rail-to-Rail
Buffer Output Voltage		Rail-to-Rail
ESD Ratings ⁽²⁾	Human Body Model	2kV
	Machine Model	150V

- (1) Absolute maximum ratings are limits beyond which damage to the device may occur. Operating Ratings are conditions for which the device is intended to be functional, but device parameter specifications may not be ensured. For specific specifications and test conditions, see the Electrical Characteristics.
- (2) The human body model is a 100 pF capacitor discharged through a 1.5kΩ resistor into each pin. The machine model is a 200pF capacitor discharged directly into each pin.

Operating Conditions

Operating Temperature	-40°C to +125°C
Storage Temperature	-65°C to +150°C
Supply Voltage, V _{IN}	2.2V to 7.5V
V _{SW} Voltage	17V
Supply Gamma Buffer, Vs+	4V to 14V

Electrical Characteristics

Specifications in standard type face are for $T_J = 25^{\circ}\text{C}$ and those with **boldface type** apply over the full **Operating Temperature Range** ($T_J = -40^{\circ}\text{C}$ to +125°C). Unless otherwise specified, $V_{IN} = 2.2\text{V}$ and $V_{S+} = 8\text{V}$.

Switching R	egulator						
Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ ⁽²⁾	Max ⁽¹⁾	Units	
IQ	Quiescent Current	Not Switching, FSCLT = 0V		1.6	2		
		Not Switching, FSCLT = V _{IN}		1.65	2.2	4	
		Switching, FSCLT = 0V		2.5	3	mA	
		Switching, FSCLT = V _{IN}		3.4	4		
		Shutdown mode		6	15	μΑ	
V _{FB}	Feedback Voltage		1.239	1.265	1.291	V	
%V _{FB} /ΔV _{IN}	Feedback Voltage Line Regulation			0.03	0.05	%/V	
I _{CL}	Switch Current Limit (3)	V _{IN} = 2.5V, V _{OUT} = 8V		1.4		Α	
R _{DSON}	Switch R _{DSON} ⁽⁴⁾	V _{IN} = 2.7V		170		mΩ	
l _B	FB Pin Bias Current ⁽⁵⁾			30	90	nA	
V _{IN}	Input Voltage Range		2.2		7.5	V	
lss	Soft Start Current		5	11	15	μΑ	
T _{SS}	Internal Soft Start Ramp Time	FSLCT = 0V		6.7	12	mS	
g _m	Error Amp Transconductance	$\Delta I = 5\mu A$	60	135	250	μmho	

⁽¹⁾ All limits ensured at room temperature (standard typeface) and at temperature extremes (bold typeface). All room temperature limits are 100% production tested or ensured through statistical analysis. All limits at temperature extremes are specified via correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).

Product Folder Links: LM3211

⁽²⁾ Typical numbers are at 25°C and represent the most likely norm.

⁽³⁾ Duty cycle affects current limit due to ramp generator. See Switch Current Limit vs. V_{IN} and Switch Current Limit vs. Temperature graphs in the Typical Performance Characteristics section.

⁽⁴⁾ See Typical Performance Characteristics section for Tri-Temperature data for R_{DSON} vs. V_{IN}.

⁽⁵⁾ Bias current flows into FB pin.



Electrical Characteristics (continued)

Specifications in standard type face are for $T_J = 25^{\circ}\text{C}$ and those with **boldface type** apply over the full **Operating Temperature Range** ($T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$). Unless otherwise specified, $V_{IN} = 2.2\text{V}$ and $V_{S+} = 8\text{V}$.

Switching R	egulator						
Symbol Parameter		Conditions	Min ⁽¹⁾	Typ ⁽²⁾	Max ⁽¹⁾	Units	
A _V	Error Amp Voltage Gain			135		V/V	
D _{MAX}	Maximum Duty Cycle		78	85		%	
f _S	Switching Frequency	FSLCT = 0V	500	600	700	kHz	
		FSLCT = V _{IN}	0.9	1.25	1.5	MHz	
IL	Switch Leakage Current	V _{SW} = 17V		0.185	20	μA	
SHDN	SHDN Threshold	Output High	0.85	0.6		V	
		Output Low		0.6	0.3	V	
I _{SHDN}	Shutdown Pin Current	0V ≤ SHDN ≤ V _{IN}		0.5	1	μΑ	
UVP	On Threshold		1.8	1.9	2	V	
	Off Threshold		1.7	1.8	1.9	V	
	Hysteresis			100		mV	

Electrical Characteristics

Specifications in standard type face are for $T_J = 25^{\circ}\text{C}$ and those with **boldface type** apply over the full **Operating Temperature Range** ($T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$). Unless otherwise specified, $V_{IN} = 2.2 \text{V}$ and $V_{S+} = 8 \text{V}$.

BUFFERS				T			
Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ ⁽²⁾	Max ⁽¹⁾	Units	
Vos	Input offset voltage			2.5	10	mV	
$\Delta V_{os}/\Delta T$	Offset Voltage Drift			8		μV/°C	
I _B	Input Bias Current			170	800	nA	
CMVR	Input Common-mode Voltage Range		0.05		Vs+-0.05	V	
Z _{IN}	Input Impedance			400		kΩ	
C _{IN}	Input Capacitance			1		pF	
l _{out}	Continuous Output Current	Vs+=8V, Source	30	39	47		
		Vs+=8V, Sink	-45	-37	-27		
		Vs+=12V, Source	35	48	59	mA	
		Vs+=12V, Sink	-54	-44	-32		
V _{OUT} Swing		R _L =10k, Vo min.			0.075		
		R _L =10k, Vo max.	7.88				
		R _L =2k, Vo min.			0.075	V	
		R _L =2k, Vo max.	7.85				
A _{VCL}	Voltage Gain	$R_L = 2 k\Omega$ $R_L = 10 k\Omega$	0.994 0.9985	0.998 0.9999		V/V	
NL	Gain Linearity	R_L =2 k Ω , Buffer input=0.5 to (Vs+-0.5V)		0.01		%	
Vs+	Supply Voltage		4		12	V	
PSRR	Power Supply Rejection Ratio	Vs+ = 4 to 12V		90	316	μV/V	
ls+	Supply Current/Amplifier	Vo = Vs+/2, No Load		0.75	1.2	mA	
SR	Slew Rate	C _L =150pf		5.3		V/µs	
BW	Bandwidth	-3dB,R _L =10 kΩ, C_L =100pf		3		MHz	
ФΜ	Phase Margin	C _L =100pf		78		Deg°	

⁽¹⁾ All limits ensured at room temperature (standard typeface) and at temperature extremes (bold typeface). All room temperature limits are 100% production tested or ensured through statistical analysis. All limits at temperature extremes are specified via correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).

Typical numbers are at 25°C and represent the most likely norm.



Typical Performance Characteristics

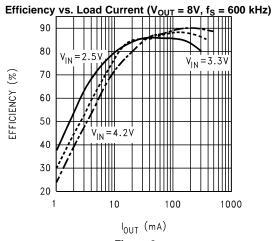
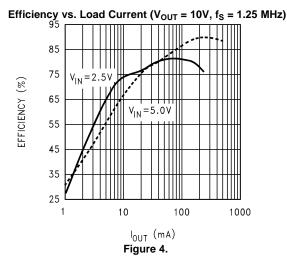
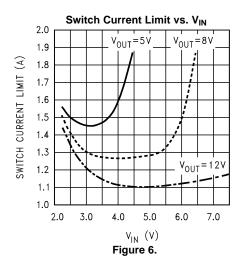
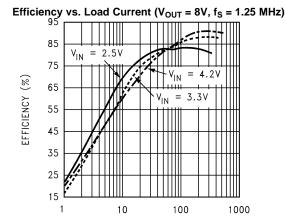


Figure 2.









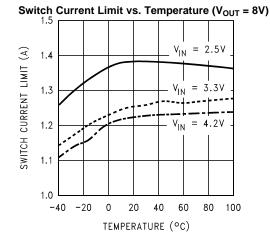


Figure 5.

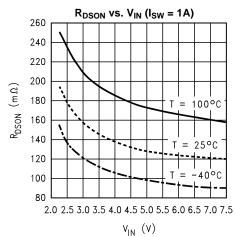
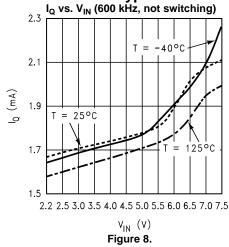
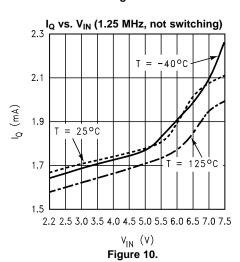


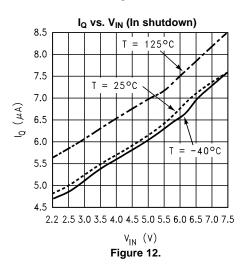
Figure 7.

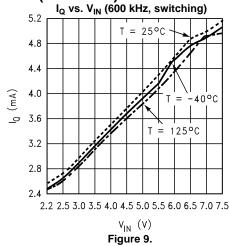


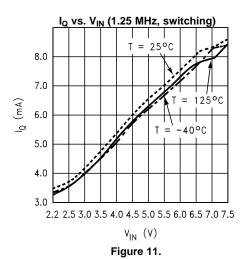


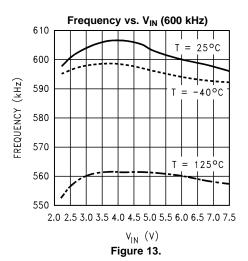












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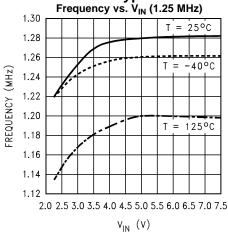


Figure 14.

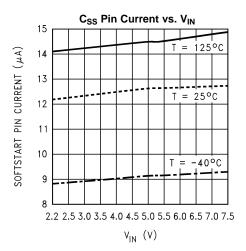
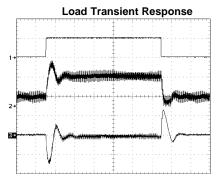


Figure 16.

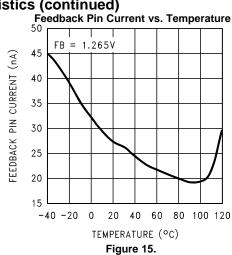


 $V_{OUT} = 8V, V_{IN} = 3V, F = 600kHz$

- 1. Load, 80mA to 260mA to 80mA
- 2. I_L, 500mA/div, DC
- 3. V_{OUT}, 200mV/div, AC

 $T = 100\mu s/div$

Figure 18.



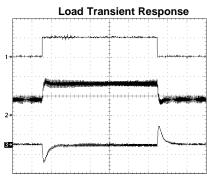
Load Transient Response

 $V_{OUT} = 8V, V_{IN} = 3V, F = 1.25MHz$

- 1. Load, 80mA to 260mA to 80mA
- 2. I_L, 500mA/div, DC
- 3. V_{OUT}, 100mV/div, AC

 $T = 100\mu s/div$

Figure 17.



 $V_{OUT} = 10V, V_{IN} = 5V, F = 1.25MHz$

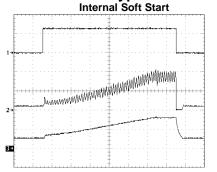
- 1. Load, 195mA to 385mA to 195mA
- 2. I_L, 500mA/div, DC
- 3. V_{OUT}, 500mV/div, AC

 $T = 100\mu s/div$

Figure 19.



Typical Performance Characteristics (continued)

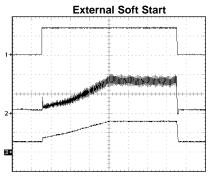


 V_{OUT} = 8V, V_{IN} = 3V, R_{LOAD} = 27 Ω , C_{SS} = none, F = 600kHz

- 1. SHDN, 1V/div, DC
- 2. I₁, 500mA/div, DC
- 3. V_{OUT}, 5V/div, DC

T = 1ms/div

Figure 20.

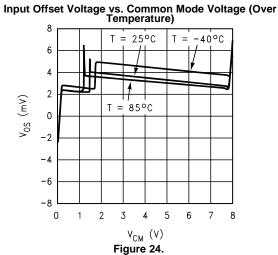


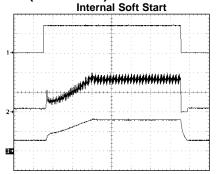
 $V_{OUT} = 8V, \ V_{IN} = 3V, \ R_{LOAD} = 27\Omega, \ C_{SS} = 330nF, \ F = 1.25MHz$

- 1. SHDN, 1V/div, DC
- 2. I_L, 500mA/div, DC
- 3. V_{OUT}, 5V/div, DC

T = 4ms/div

Figure 22.





 V_{OUT} = 8V, V_{IN} = 3V, R_{LOAD} = 27 Ω , C_{SS} = none, F = 1.25MHz

- 1. SHDN, 1V/div, DC
- 2. I_L, 500mA/div, DC
- 3. V_{OUT}, 5V/div, DC

T = 1 ms/div

Figure 21.

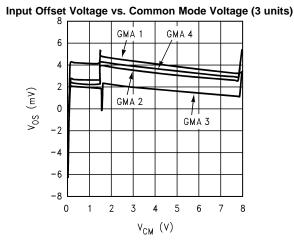
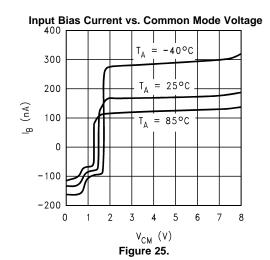
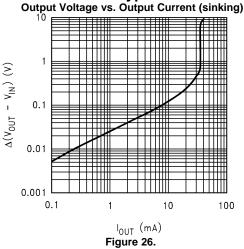
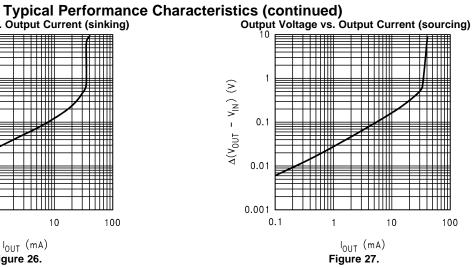


Figure 23.

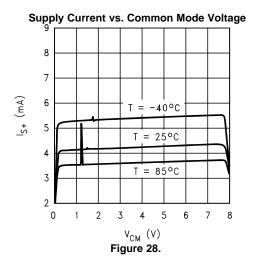




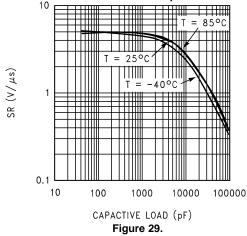




Large Signal Step Response



Positive Slew Rate vs. Capacitive Load



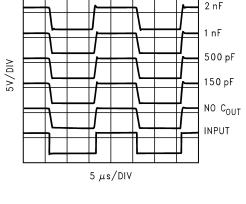
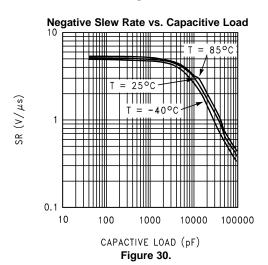


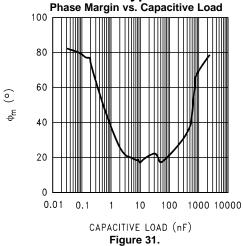
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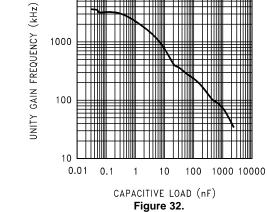


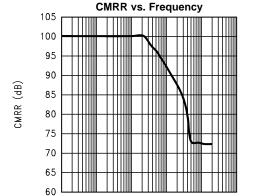
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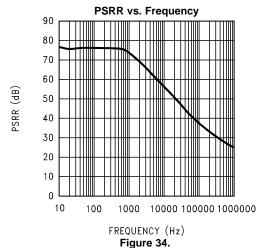


Typical Performance Characteristics (continued) ovs. Capacitive Load Unity Gain Frequency vs. Capacitive Load









FREQUENCY (Hz) Figure 33.

10000 100000 1000000

10

100



OPERATION

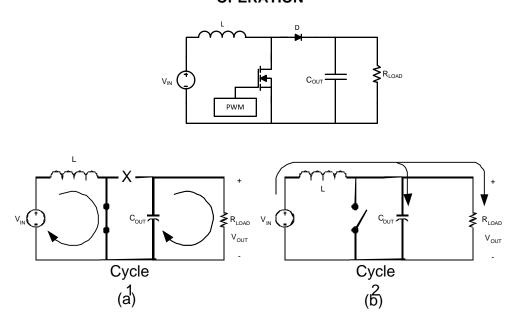


Figure 35. Simplified Boost Converter Diagram (a) First Cycle of Operation (b) Second Cycle Of Operation

CONTINUOUS CONDUCTION MODE

The LM3211 is a current-mode, PWM boost regulator. A boost regulator steps the input voltage up to a higher output voltage. In continuous conduction mode (when the inductor current never reaches zero at steady state), the boost regulator operates in two cycles.

In the first cycle of operation, shown in Figure 35 (a), the transistor is closed and the diode is reverse biased. Energy is collected in the inductor and the load current is supplied by C_{OUT} .

The second cycle is shown in Figure 35 (b). During this cycle, the transistor is open and the diode is forward biased. The energy stored in the inductor is transferred to the load and output capacitor.

The ratio of these two cycles determines the output voltage. The output voltage is defined approximately as:

$$V_{OUT} = \frac{V_{IN}}{1-D}$$
, $D' = (1-D) = \frac{V_{IN}}{V_{OUT}}$ (2)

where D is the duty cycle of the switch, D and D' will be required for design calculations

SETTING THE OUTPUT VOLTAGE

The output voltage is set using the feedback pin and a resistor divider connected to the output as shown in the typical operating circuit. The feedback pin voltage is 1.265V, so the ratio of the feedback resistors sets the output voltage according to the following equation:

$$R1 = R2 \left(\frac{V_{OUT}}{1.265 V} - 1 \right)$$
 (3)



SOFT-START CAPACITOR

The LM3211 has patented internal circuitry that is used to limit the inductor inrush current on start-up. This inrush current limiting circuitry serves as a soft-start. However, many applications may require much more soft-start than what is available with the internal circuitry. The external SS pin is used to tailor the soft-start for a specific application. A 11µA current charges the external soft-start capacitor, Css. The soft-start time can be estimated as:

$$Tss = Css^*0.6V/11\mu A \tag{4}$$

The minimum soft-start time is set by the internal soft-start circuitry, typically 7ms for 600kHz operation and approximately half that for 1.25MHz operation. Only longer soft-start times may be implemented using the SS pin and a capacitor C_{SS} . If a shorter time is designed for using the above equation, the internal soft-start circuitry will override it.

Due to the unique nature of the dual internal/external softstart, care was taken in the design to ensure temperature stable operation. As you can see with the Iss data in the Electrical Characteristic table and the graph "Soft-Start Current vs. V_{IN} " in the Typical Performance Characteristics section, the soft start current has a temperature coefficient and would lead one to believe there would be significant variation with temperature. Though the current has a temperature coefficient the actual programmed external soft start time does not show this extreme of a temperature variation. As you can see in the following transient plots:

 $V_{OUT} = 8V$, $V_{IN} = 2.5V$, $R_L = 27\Omega$, $C_{SS} = 330nF$, T = 4ms/div, F = 1.25MHz.

Trace

- 1. SHDN, 1V/div, DC Coupled
- 2. I_I, 0.5A/div, DC Coupled
- 3. V_{OUT}, 5V/div, DC Coupled

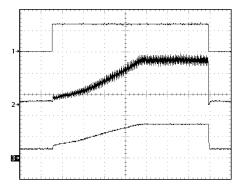


Figure 36. $T_A = -20$ °C

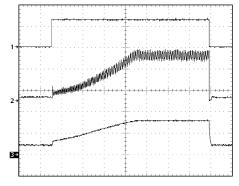


Figure 37. $T_A = 27^{\circ}C$



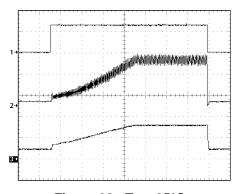


Figure 38. $T_A = 85^{\circ}C$

When programming the softstart time externally, simply use the equation given in the SOFT-START CAPACITOR section above. This equation uses the typical room temperature value of the soft start current, $11\mu A$, to set the soft start time.

INTRODUCTION TO COMPENSATION

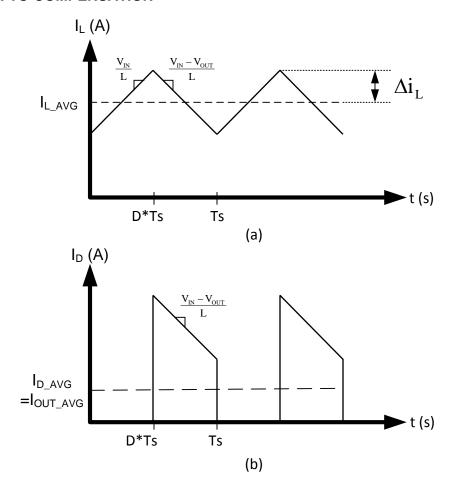


Figure 39. (a) Inductor current. (b) Diode current.

The LM3211 is a current mode PWM boost converter. The signal flow of this control scheme has two feedback loops, one that senses switch current and one that senses output voltage.



To keep a current programmed control converter stable above duty cycles of 50%, the inductor must meet certain criteria. The inductor, along with input and output voltage, will determine the slope of the current through the inductor (see Figure 39 (a)). If the slope of the inductor current is too great, the circuit will be unstable above duty cycles of 50%. A 10µH inductor is recommended for most 600 kHz applications, while a 4.7µH inductor may be used for most 1.25 MHz applications. If the duty cycle is approaching the maximum of 85%, it may be necessary to increase the inductance by as much as 2X. See INDUCTOR AND DIODE SELECTION for more detailed inductor sizing.

The LM3211 provides a compensation pin (V_C) to customize the voltage loop feedback. It is recommended that a series combination of R_C and C_C be used for the compensation network, as shown in the typical application circuit. For any given application, there exists a unique combination of R_C and C_C that will optimize the performance of the LM3211 circuit in terms of its transient response. The series combination of R_C and C_C introduces a pole-zero pair according to the following equations:

$$f_{ZC} = \frac{1}{2\pi R_C C_C} Hz \tag{5}$$

$$f_{PC} = \frac{1}{2\pi (R_C + R_O)C_C} Hz$$
 (6)

where R_O is the output impedance of the error amplifier, approximately $1M\Omega$. For most applications, performance can be optimized by choosing values within the range $5k\Omega \le R_C \le 60k\Omega$ (R_C can be up to $200k\Omega$ if C_{C2} is used, see HIGH OUTPUT CAPACITOR ESR COMPENSATION) and $680pF \le C_C \le 4.7nF$. Refer to the Application Information section for recommended values for specific circuits and conditions. Refer to the Compensation section for other design requirement.

COMPENSATION FOR BOOST DC/DC

This section will present a general design procedure to help insure a stable and operational circuit. The designs in this datasheet are optimized for particular requirements. If different conversions are required, some of the components may need to be changed to ensure stability. Below is a set of general guidelines in designing a stable circuit for continuous conduction operation, in most all cases this will provide for stability during discontinuous operation as well. The power components and their effects will be determined first, then the compensation components will be chosen to produce stability.

INDUCTOR AND DIODE SELECTION

Although the inductor sizes mentioned earlier are fine for most applications, a more exact value can be calculated. To ensure stability at duty cycles above 50%, the inductor must have some minimum value determined by the minimum input voltage and the maximum output voltage. This equation is:

$$L > \frac{V_{\text{IN}}R_{\text{DSON}}}{0.144 \text{ fs}} \left[\frac{\left(\frac{D}{D'}\right)^2 - 1}{\left(\frac{D}{D'}\right) + 1} \right] (\text{in H})$$

$$(7)$$

where fs is the switching frequency, D is the duty cycle, and R_{DSON} is the ON resistance of the internal switch taken from the graph " R_{DSON} vs. V_{IN} " in the *Typical Performance Characteristics* section. This equation is only good for duty cycles greater than 50% (D>0.5), for duty cycles less than 50% the recommended values may be used. The corresponding inductor current ripple as shown in Figure 39 (a) is given by:

$$\Delta i_{L} = \frac{V_{IN}D}{2Lfs} \quad \text{(in Amps)}$$
 (8)

The inductor ripple current is important for a few reasons. One reason is because the peak switch current will be the average inductor current (input current or I_{LOAD}/D') plus Δi_L . As a side note, discontinuous operation occurs when the inductor current falls to zero during a switching cycle, or Δi_L is greater than the average inductor current. Therefore, continuous conduction mode occurs when Δi_L is less than the average inductor current. Care must be taken to make sure that the switch will not reach its current limit during normal operation. The inductor must also be sized accordingly. It should have a saturation current rating higher than the peak inductor current expected. The output voltage ripple is also affected by the total ripple current.

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The output diode for a boost regulator must be chosen correctly depending on the output voltage and the output current. The typical current waveform for the diode in continuous conduction mode is shown in Figure 39 (b). The diode must be rated for a reverse voltage equal to or greater than the output voltage used. The average current rating must be greater than the maximum load current expected, and the peak current rating must be greater than the peak inductor current. During short circuit testing, or if short circuit conditions are possible in the application, the diode current rating must exceed the switch current limit. Using Schottky diodes with lower forward voltage drop will decrease power dissipation and increase efficiency.

DC GAIN AND OPEN-LOOP GAIN

Since the control stage of the converter forms a complete feedback loop with the power components, it forms a closed-loop system that must be stabilized to avoid positive feedback and instability. A value for open-loop DC gain will be required, from which you can calculate, or place, poles and zeros to determine the crossover frequency and the phase margin. A high phase margin (greater than 45°) is desired for the best stability and transient response. For the purpose of stabilizing the LM3211, choosing a crossover point well below where the right half plane zero is located will ensure sufficient phase margin. A discussion of the right half plane zero and checking the crossover using the DC gain will follow.

INPUT AND OUTPUT CAPACITOR SELECTION

The switching action of a boost regulator causes a triangular voltage waveform at the input. A capacitor is required to reduce the input ripple and noise for proper operation of the regulator. The size used is dependant on the application and board layout. If the regulator will be loaded uniformly, with very little load changes, and at lower current outputs, the input capacitor size can often be reduced. The size can also be reduced if the input of the regulator is very close to the source output. The size will generally need to be larger for applications where the regulator is supplying nearly the maximum rated output or if large load steps are expected. A minimum value of 10µF should be used for the less stressful conditions while a 22µF to 47µF capacitor may be required for higher power and dynamic loads. Larger values and/or lower ESR may be needed if the application requires very low ripple on the input source voltage.

The choice of output capacitors is also somewhat arbitrary and depends on the design requirements for output voltage ripple. It is recommended that low ESR (Equivalent Series Resistance, denoted R_{ESR}) capacitors be used such as ceramic, polymer electrolytic, or low ESR tantalum. Higher ESR capacitors may be used but will require more compensation which will be explained later on in the section. The ESR is also important because it determines the peak to peak output voltage ripple according to the approximate equation:

$$\Delta V_{OUT} \cong 2\Delta i_L R_{ESR}$$
 (in Volts) (9)

A minimum value of 10µF is recommended and may be increased to a larger value. After choosing the output capacitor you can determine a pole-zero pair introduced into the control loop by the following equations:

$$f_{P1} = \frac{1}{2\pi (R_{ESR} + R_L)C_{OUT}}$$
 (in Hz) (10)

$$f_{Z1} = \frac{1}{2\pi R_{ESR} C_{OUT}} \text{ (in Hz)}$$

$$\tag{11}$$

Where R_L is the minimum load resistance corresponding to the maximum load current. The zero created by the ESR of the output capacitor is generally very high frequency if the ESR is small. If low ESR capacitors are used it can be neglected. If higher ESR capacitors are used see the HIGH OUTPUT CAPACITOR ESR COMPENSATION section.

RIGHT HALF PLANE ZERO

A current mode control boost regulator has an inherent right half plane zero (RHP zero). This zero has the effect of a zero in the gain plot, causing an imposed +20dB/decade on the rolloff, but has the effect of a pole in the phase, subtracting another 90° in the phase plot. This can cause undesirable effects if the control loop is influenced by this zero. To ensure the RHP zero does not cause instability issues, the control loop should be designed to have a bandwidth of less than ½ the frequency of the RHP zero. This zero occurs at a frequency of:

$$RHPzero = \frac{V_{OUT}(D')^2}{2\pi I_{LOAD}L} \text{ (in Hz)}$$
(12)

where I_{I OAD} is the maximum load current.



SELECTING THE COMPENSATION COMPONENTS

The first step in selecting the compensation components R_C and C_C is to set a dominant low frequency pole in the control loop. Simply choose values for R_C and C_C within the ranges given in the INTRODUCTION TO COMPENSATION section to set this pole in the area of 10Hz to 500Hz. The frequency of the pole created is determined by the equation:

$$f_{PC} = \frac{1}{2\pi(R_C + R_0)C_C}$$
 (in Hz) (13)

where R_O is the output impedance of the error amplifier, approximately $1M\Omega$. Since R_C is generally much less than R_O , it does not have much effect on the above equation and can be neglected until a value is chosen to set the zero f_{ZC} . f_{ZC} is created to cancel out the pole created by the output capacitor, f_{P1} . The output capacitor pole will shift with different load currents as shown by the equation, so setting the zero is not exact. Determine the range of f_{P1} over the expected loads and then set the zero f_{ZC} to a point approximately in the middle. The frequency of this zero is determined by:

$$f_{ZC} = \frac{1}{2\pi C_C R_C} \text{ (in Hz)}$$
 (14)

Now R_C can be chosen with the selected value for C_C . Check to make sure that the pole f_{PC} is still in the 10Hz to 500Hz range, change each value slightly if needed to ensure both component values are in the recommended range. After checking the design at the end of this section, these values can be changed a little more to optimize performance if desired. This is best done in the lab on a bench, checking the load step response with different values until the ringing and overshoot on the output voltage at the edge of the load steps is minimal. This should produce a stable, high performance circuit. For improved transient response, higher values of R_C should be chosen. This will improve the overall bandwidth which makes the regulator respond more quickly to transients. If more detail is required, or the most optimal performance is desired, refer to a more in depth discussion of compensating current mode DC/DC switching regulators.

HIGH OUTPUT CAPACITOR ESR COMPENSATION

When using an output capacitor with a high ESR value, or just to improve the overall phase margin of the control loop, another pole may be introduced to cancel the zero created by the ESR. This is accomplished by adding another capacitor, C_{C2} , directly from the compensation pin V_C to ground, in parallel with the series combination of R_C and C_C . The pole should be placed at the same frequency as f_{Z1} , the ESR zero. The equation for this pole follows:

$$f_{PC2} = \frac{1}{2\pi C_{C2}(R_C /\!/R_O)} \text{ (in Hz)}$$
 (15)

To ensure this equation is valid, and that C_{C2} can be used without negatively impacting the effects of R_C and C_C , f_{PC2} must be greater than $10f_{ZC}$.

CHECKING THE DESIGN

The final step is to check the design. This is to ensure a bandwidth of $\frac{1}{2}$ or less of the frequency of the RHP zero. This is done by calculating the open-loop DC gain, A_{DC} . After this value is known, you can calculate the crossover visually by placing a -20dB/decade slope at each pole, and a +20dB/decade slope for each zero. The point at which the gain plot crosses unity gain, or 0dB, is the crossover frequency. If the crossover frequency is less than $\frac{1}{2}$ the RHP zero, the phase margin should be high enough for stability. The phase margin can also be improved by adding C_{C2} as discussed earlier in the section. The equation for A_{DC} is given below with additional equations required for the calculation:

$$A_{DC(DB)} = 20log_{10} \left\langle \left(\frac{R_{FB2}}{R_{FB1} + R_{FB2}} \right) \frac{g_m R_O D'}{R_{DSON}} \{ [(\omega c Leff) / / R_L] / / R_L \} \right\rangle \text{ (in dB)}$$
(16)

$$\omega c \simeq \frac{2fs}{nD'} \quad \text{(in rad/s)} \tag{17}$$

$$Leff = \frac{L}{(D')^2} \tag{18}$$

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$$n = 1 + \frac{2mc}{m1}$$
 (no unit) (19)

$$mc \approx 0.072 fs (in V/s)$$
 (20)

$$m1 \cong \frac{V_{IN}R_{DSON}}{L} \quad (in \ V/s) \tag{21}$$

where R_L is the minimum load resistance, V_{IN} is the maximum input voltage, g_m is the error amplifier transconductance found in the Electrical Characteristics table, and R_{DSON} is the value chosen from the graph "R_{DSON} vs. V_{IN}" in the *Typical Performance Characteristics* section.

BUFFER COMPENSATION

The Gamma buffers in the LM3211 are internally compensated. They will remain stable with no capacitive load while sourcing or sinking current. Any capacitance presented by a load in an application will only provide further stability.

LAYOUT CONSIDERATIONS

The LM3211 uses two separate ground connections, GND for the driver and NMOS power device of the boost regulator and AGND for the sensitive analog control circuitry of the boost regulator and the V_{COM} and Gamma buffers. The AGND and GND pins should be tied directly together at the package, see Figure 40 and Figure 41. The feedback, softstart, and compensation networks should be connected directly to a dedicated analog ground plane and this ground plane must connect to the AGND pin, as in Figure 40. If no analog ground plane is available then the ground connections of the feedback, softstart, and compensation networks must tie directly to the AGND pin, as show in Figure 41. Connecting these networks to the GND pin can inject noise into the system and effect performance. For 600kHz operation the FSLCT pin should be tied to an analog ground plane or directly to the AGND pin. For 1.25MHz operation the FSLCT pin should be tied to the V_{IN} pin.

The input bypass capacitor CIN must be placed close to the IC. This will reduce copper trace resistance which effects input voltage ripple of the IC. For additional input voltage filtering, a 100nF bypass capacitor can be placed in parallel with C_{IN} , close to the V_{IN} pin, to shunt any high frequency noise to ground. The output capacitor, C_{OUT} , should also be placed close to the IC. Any copper trace connections for the C_{OUT} capacitor can increase the series resistance, which directly effects output voltage ripple and efficiency. The feedback network, resistors R1 and R2, should be kept close to the FB pin, and away from the inductor, to minimize copper trace connections that can inject noise into the system. Trace connections made to the inductor and schottky diode should be minimized to reduce power dissipation and increase overall efficiency.

The layout of the Gamma buffer traces is important to minimize noise injected into them. Route all input and output traces for the buffers away from the inductor and the high power switching traces used for the boost switcher. For best performance route these traces on the opposite side of the board from the high current switching traces and use a ground plane between the two sides for shielding.

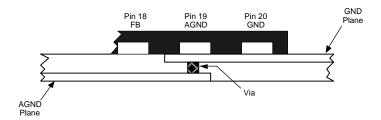


Figure 40. Multi-Layer Layout

Product Folder Links: LM3211



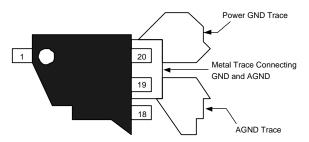


Figure 41. Single Layer Layout

Application Information

Table 1. Some recommended Inductors (others may be used)

Manufacturer	Inductor	Contact Information
Coilcraft	DO3316 series	www.coilcraft.com
Coiltronics	DRQ73 series	www.cooperet.com
Pulse	P0751 series	www.pulseeng.com
Sumida	CDRH8D28 series	www.sumida.com

Table 2. Some recommended Input and Output Capacitors (others may be used)

Manufacturer	Capacitor	Contact Information			
Vishay Sprague	293D, 592D, and 595D series tantalum	www.vishay.com			
Taiyo Yuden	High capacitance MLCC ceramic	www.t-yuden.com			
Cornell Dubilier	ESRD seriec Polymer Aluminum Electrolytic SPV and AFK series V-chip series	www.cde.com			
Panasonic	High capacitance MLCC ceramic EEJ-L series tantalum	www.panasonic.com			

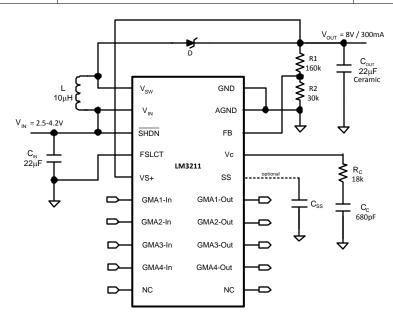


Figure 42. 600kHz, 8V Application



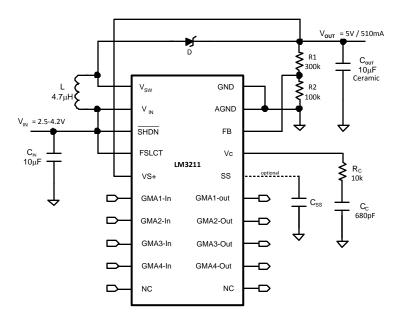


Figure 43. 1.25MHz, 5V Application

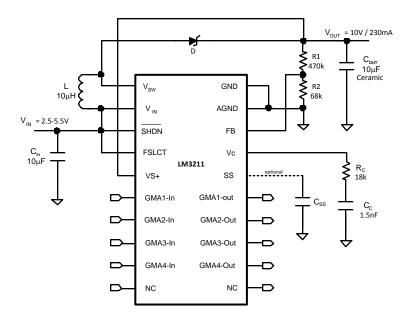


Figure 44. 1.25MHz, 10V Application



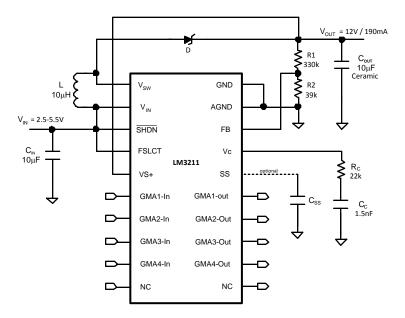


Figure 45. 1.25MHz, 12V Application





REVISION HISTORY

Cł	hanges from Revision A (March 2013) to Revision B	Page
•	Changed layout of National Data Sheet to TI format	22



PACKAGE OPTION ADDENDUM

28-Mar-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
LM3211MTX-ADJ/NOPB	ACTIVE	TSSOP	PW	20	2500	Green (RoHS	CU SN	Level-1-260C-UNLIM		LM3211	Samples
						& no Sb/Br)				MTADJ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

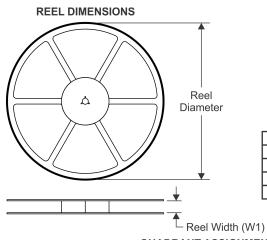
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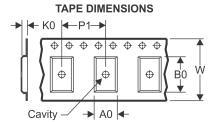
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PACKAGE MATERIALS INFORMATION

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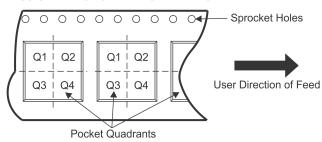
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

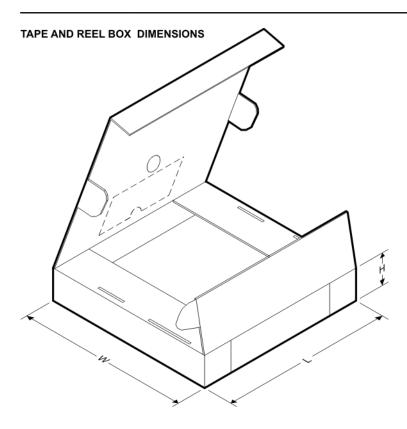


*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM3211MTX-ADJ/NOPB	TSSOP	PW	20	2500	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1

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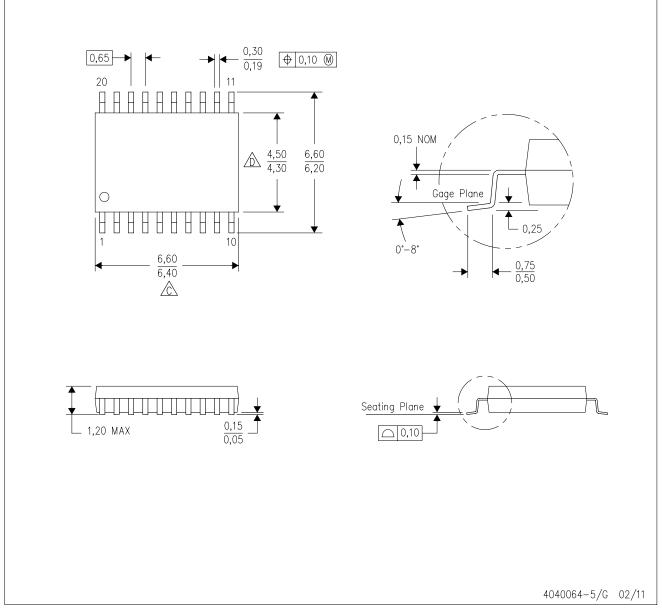


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM3211MTX-ADJ/NOPB	TSSOP	PW	20	2500	367.0	367.0	35.0

PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



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Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

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